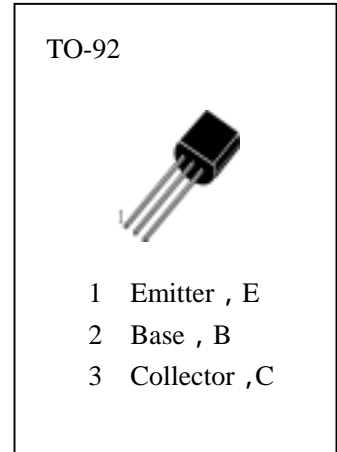




HIGH VOLTAGE TRANSISTOR

ABSOLUTE MAXIMUM RATINGS (Ta=25)

- T_{stg}—Storage Temperature..... -55~150
- T_j—Junction Temperature.....150
- P_C—Collector Dissipation.....625mW
- V_{CBO}—Collector-Base Voltage.....300V
- V_{CEO}—Collector-Emitter Voltage.....300V
- V_{EBO}—Emitter-Base Voltage.....6V
- I_C—Collector Current.....500mA



ELECTRICAL CHARACTERISTICS (Ta=25)

Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
BVCBO	Collector-Base Breakdown Voltage	300			V	I _C =100 μ A, I _E =0
BVCEO	Collector-Emitter Breakdown Voltage	300			V	I _C =1mA, I _B =0
BVEBO	Emitter-Base Breakdown Voltage	5			V	I _E =100 μ A , I _C =0
ICBO	Collector Cut-off Current			100	nA	V _{CB} =200V, I _E =0
IEBO	Emitter-Base Cut-off Current			100	nA	V _{EB} =3V, I _C =0
ICES	Collector Cut-off Current			1	μ A	V _{CE} =300V, V _{BE} =0
HFE (1)	DC Current Gain	25				V _{CE} =10V, I _C =1mA
HFE (2)		40				V _{CE} =10V, I _C =10mA
HFE (3)		40				V _{CE} =10V, I _C =30mA
VCE(sat1)	Collector- Emitter Saturation Voltage			0.5	V	I _C =20mA, I _B =2mA
VCE(sat2)				1	V	I _C =60mA, I _B =6mA
VBE(sat1)	Base-Emitter Saturation Voltage			0.9	V	I _C =20mA, I _B =2mA
f _T	Current Gain-Bandwidth Product	50			MHZ	V _{CE} =20V, I _C =10mA F=100MHZ